



Dual N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.225 at $V_{GS} = 4.5$ V	1.5	1.1 nC
	0.270 at $V_{GS} = 2.5$ V	1.5	
	0.345 at $V_{GS} = 1.8$ V	1.5	
	0.960 at $V_{GS} = 1.5$ V	0.5	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.75 mm Profile
- Typical ESD Protection 2800 V
- Rated ESD Protection 1400 V
- Compliant to RoHS Directive 2002/95/EC

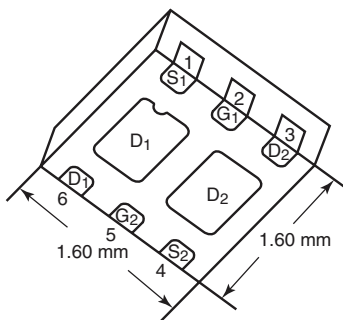


RoHS
COMPLIANT
HALOGEN
FREE

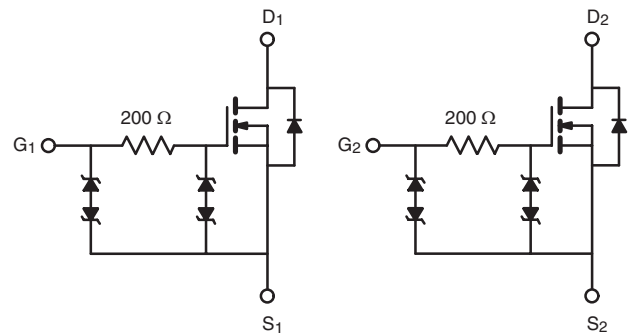
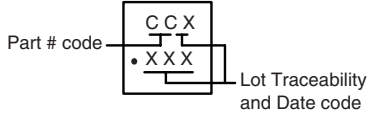
APPLICATIONS

- Load Switch for Portable Devices
- Low Voltage Load Switch

PowerPAK SC75-6L-Dual



Marking Code



Ordering Information: SiB900EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 6	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	1.5 ^a
		$T_C = 70$ °C	1.5 ^a
		$T_A = 25$ °C	1.5 ^{a, b, c}
		$T_A = 70$ °C	1.3 ^{b, c}
Pulsed Drain Current	I_{DM}	4	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	0.9 ^{b, c}
Maximum Power Dissipation	P_D	$T_C = 25$ °C	3.1
		$T_C = 70$ °C	2
		$T_A = 25$ °C	1.1 ^{b, c}
		$T_A = 70$ °C	0.7 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	$t \leq 5$ s	R_{thJA}	90	115	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	32	40	

Notes:

- a. Package limited.
b. Surface Mounted on 1" x 1" FR4 board.
c. $t = 5$ s.
d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under Steady State conditions is 125 °C/W.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ μ A		21		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-2.3			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	0.4		1.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 3$ V			± 1	μ A
		$V_{DS} = 0$ V, $V_{GS} = \pm 6$ V			± 1	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20$ V, $V_{GS} = 0$ V			1	μ A
		$V_{DS} = 20$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 4.5$ V	4			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5$ V, $I_D = 1.6$ A		0.183	0.225	Ω
		$V_{GS} = 2.5$ V, $I_D = 1.5$ A		0.220	0.270	
		$V_{GS} = 1.8$ V, $I_D = 1.3$ A		0.275	0.345	
		$V_{GS} = 1.5$ V, $I_D = 0.3$ A		0.320	0.960	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10$ V, $I_D = 1.6$ A		3.5		S
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10$ V, $V_{GS} = 4.5$ V, $I_D = 1.7$ A		1.1	1.7	nC
Gate-Source Charge	Q_{gs}		0.2			
Gate-Drain Charge	Q_{gd}		0.1			
Gate Resistance	R_g	$f = 1$ MHz		200		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10$ V, $R_L = 7.7$ Ω $I_D \cong 1.3$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω		20	30	ns
Rise Time	t_r		12	20		
Turn-Off Delay Time	$t_{d(off)}$		70	105		
Fall Time	t_f		20	30		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C			1.5	A
Pulse Diode Forward Current	I_{SM}				4	
Body Diode Voltage	V_{SD}	$I_S = 1.3$ A, $V_{GS} = 0$ V		0.9	1.2	V

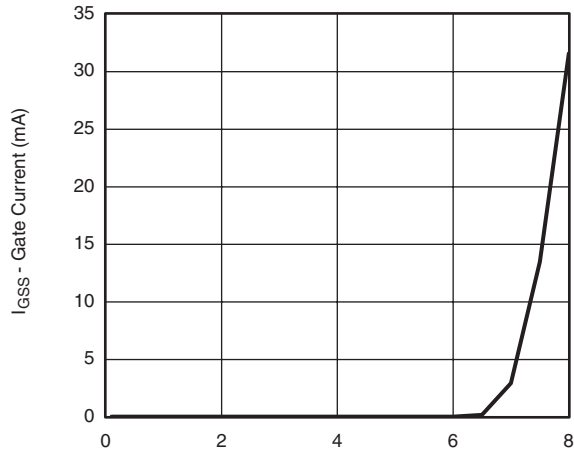
Notes:

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

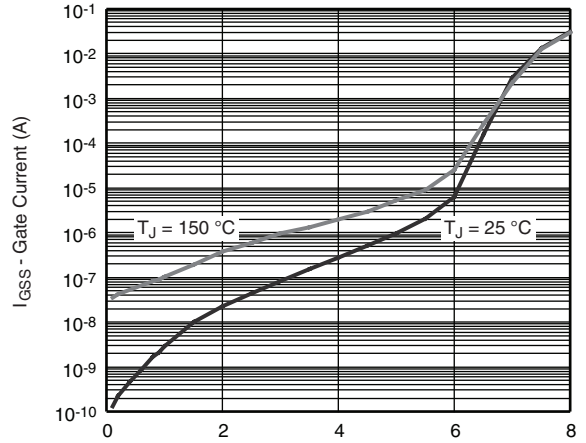
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



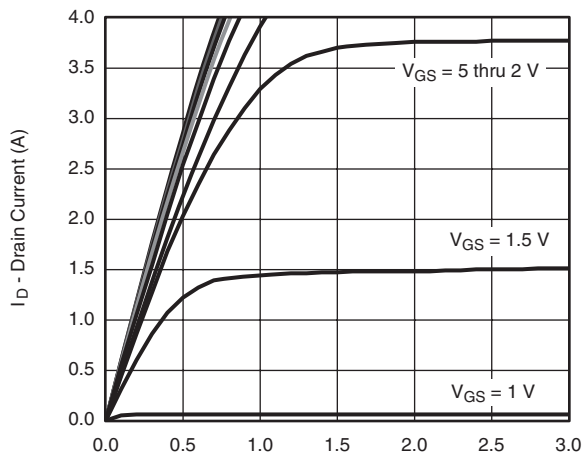
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



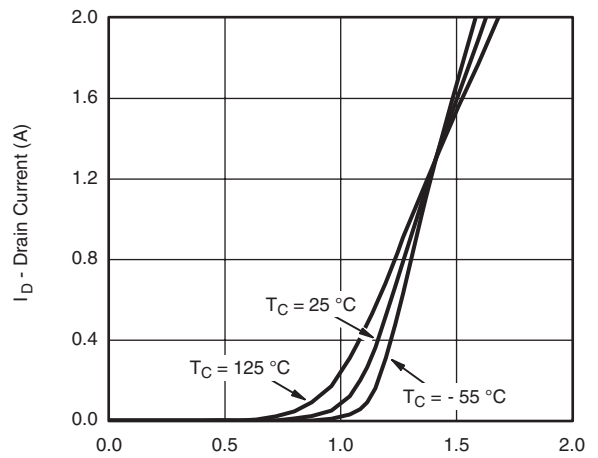
V_{GS} - Gate-to-Source Voltage (V)
Gate Current vs. Gate-to-Source Voltage



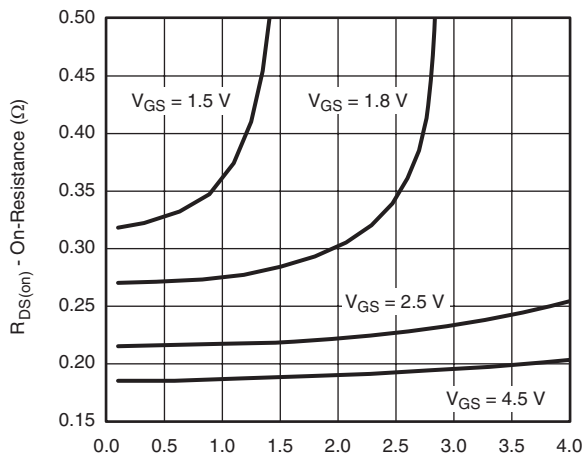
V_{GS} - Gate-to-Source Voltage (V)
Gate Current vs. Gate-to-Source Voltage



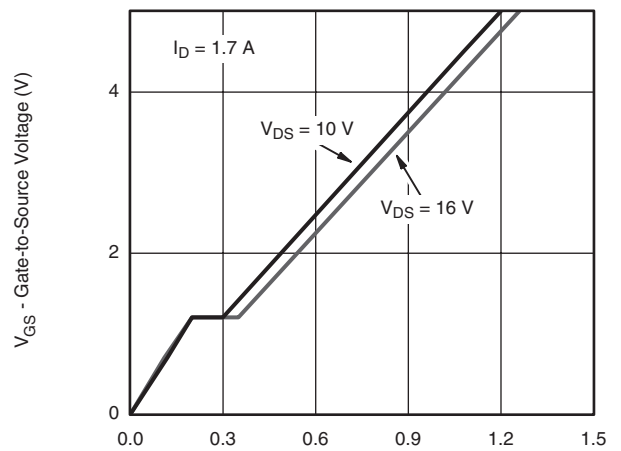
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



I_D - Drain Current (A)
On-Resistance vs. Drain Current



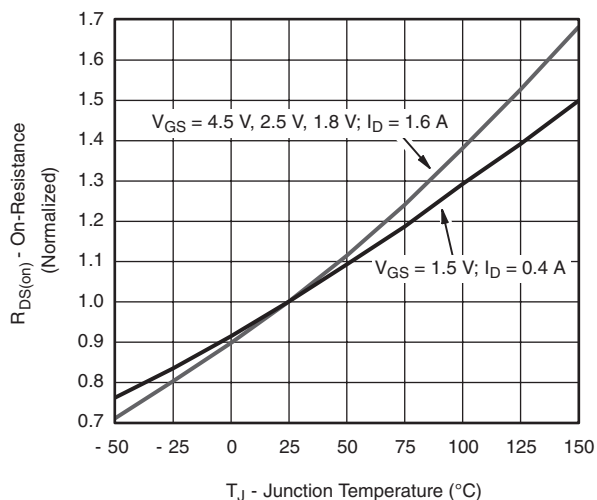
Q_g - Total Gate Charge (nC)
Gate Charge

SiB900EDK

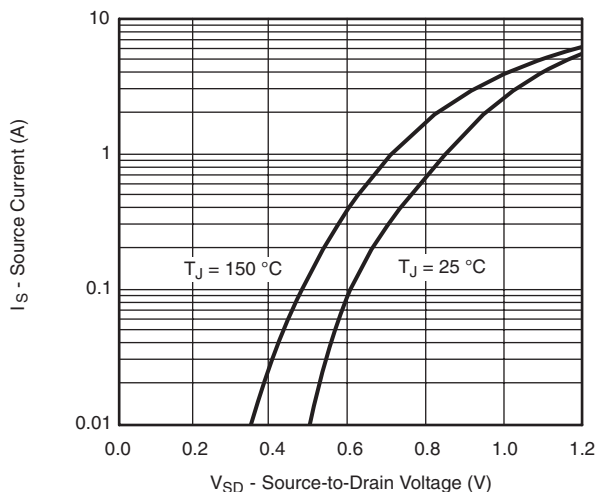
Vishay Siliconix



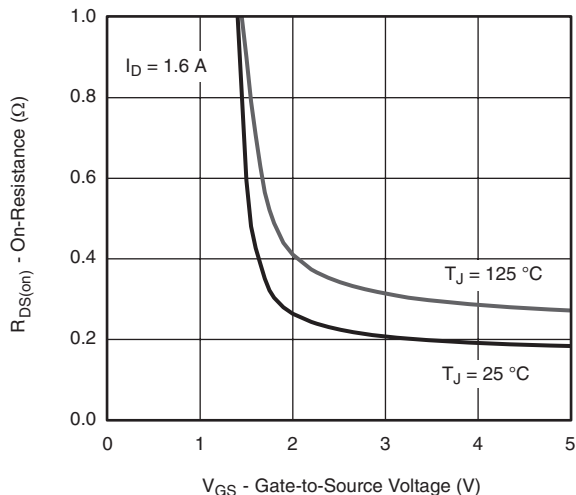
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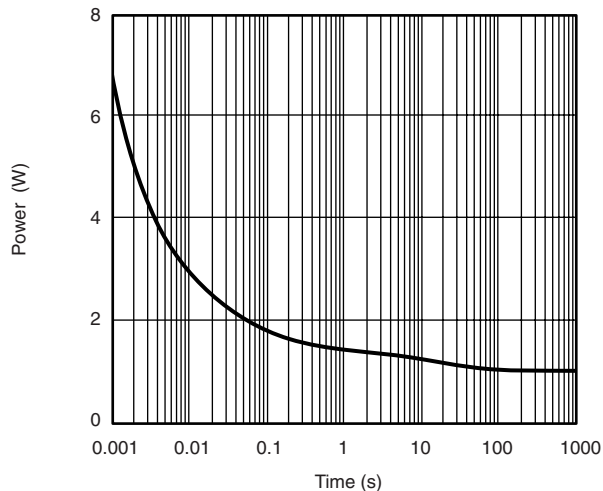
Normalized On-Resistance vs. Junction Temperature



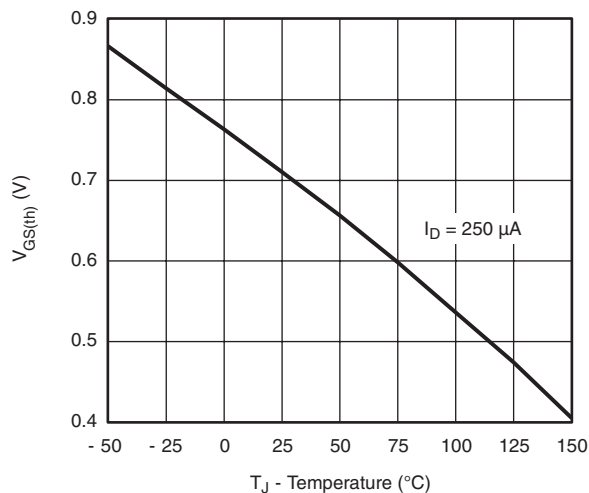
Source-Drain Diode Forward Voltage



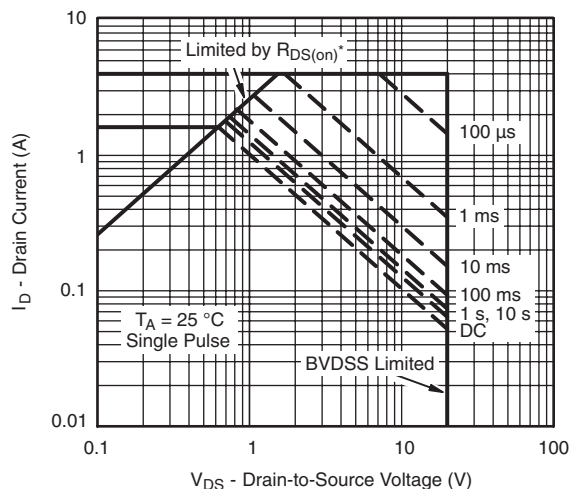
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Threshold Voltage

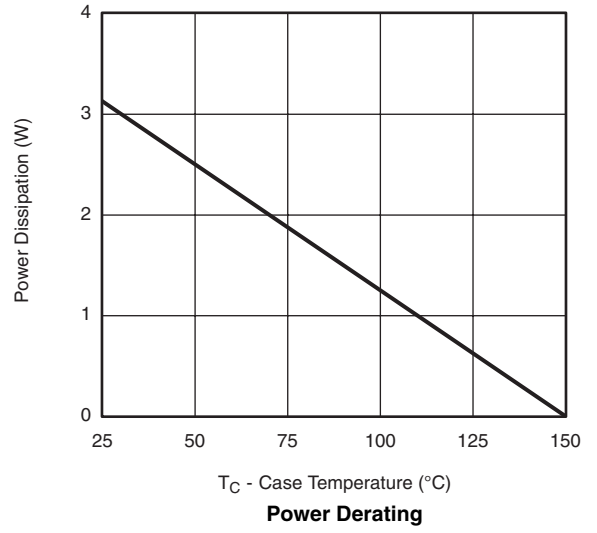
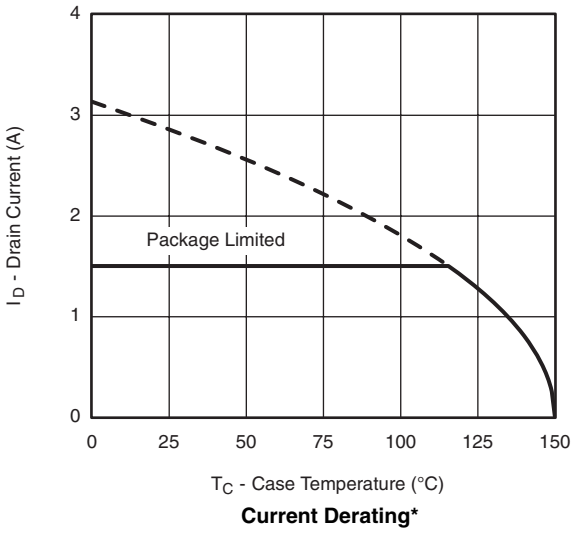


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



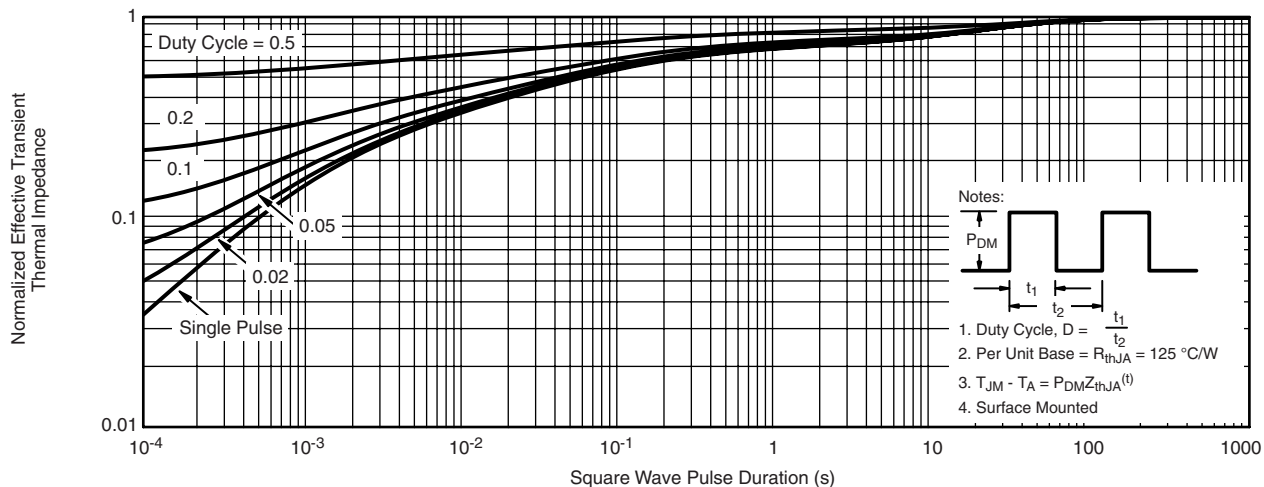
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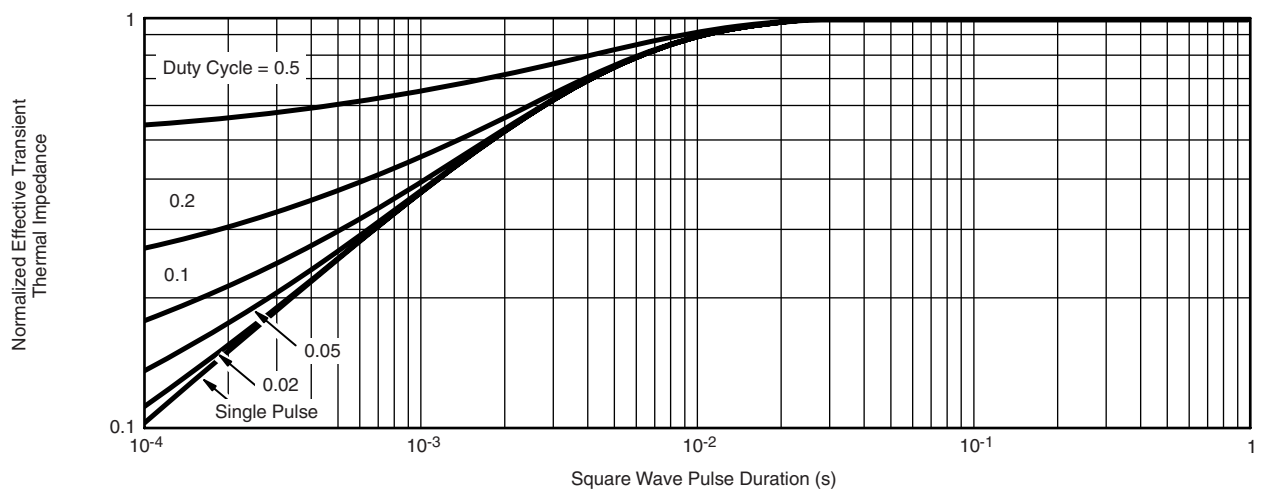
* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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